

# SOT-23 TRANSISTORS & DIODES

## SCHOTTKY BARRIER DIODES

Type	$V_{BR}$ at $I_R=10\mu A$ min. (Volts)	$V_F$ at $I_F=1mA$ max. (mV)	$I_R$ max. nA at $V_R$ (volts)		$I_F$ at $V_F=1V$ min. (mA)	$C_T$ at $V_R=0V$ $f=1MHz$ max. (pF)
			200	50		
ZC2800E	70	410	200	50	15	2.0
*ZC2810E	20	410	100	15	35	1.2
ZC2811E	15	410	100	10	20	1.2
ZC5800E	50	410	200	35	15	2.0

\*Not recommended for New Design - In (ZC2810E)

## DUAL SCHOTTKY BARRIER DIODES

Type	$V_{BR}$ at $I_R=10\mu A$ min. (Volts)	$V_F$ at $I_F=1mA$ max. (mV)	$I_R$ max. nA at $V_R$ (volts)		$I_F$ at $V_F=1V$ min. (mA)	$C_T$ at $V_R=0V$ $f=1MHz$ max. (pF)	Pinning configuration
			200	50			
BAS70-04	70	410	200	50	15	2.0	Series Common cathode Common anode
BAS70-05	70	410	200	50	15	2.0	
BAS70-06	70	410	200	50	15	2.0	

## SILICON ION IMPLANTED HYPERABRUPT TUNER DIODES

Type	Reverse breakdown Voltage $V_R$ Volts max.	Nominal capacitance at $V_R=2V$ , $f=1MHz$ $C_{tot}$ pF			Capacitance ratio $f=1MHz$ $C_2/C_{20}$		$Q$ at $V_R=3V$ $f=50MHz$ min.
		min.	typ.	max.	min.	max.	
ZC830A	25	9.0	10	11.0	4.5	6.0	300
ZC831A	25	13.5	15	16.5	4.5	6.0	300
ZC832A	25	19.8	22	24.2	5.0	6.5	200
ZC833A	25	29.7	33	36.3	5.0	6.5	200
ZC834A	25	42.3	47	51.7	5.0	6.5	200
ZC835A	25	61.2	68	74.8	5.0	6.5	100
ZC836A	25	90.0	100	110.0	5.0	6.5	100

Devices are also available with 5% and 20% tolerances. No suffix -  $\pm 20\%$  (e.g. ZC830)  
Suffix B -  $\pm 5\%$  (e.g. ZC830B)

## VARIABLE CAPACITANCE TUNER DIODES

Type	Reverse Breakdown Voltage $V_R$ Volts	Nominal Capacitance at $f=1MHz$ $C_{tot}$ pF				Capacitance ratio at $f=1MHz$ $C_3/C_{25}$			$Q$ at $V_R=3V$ $f=50MHz$ Typ.
		Min.	Typ.	Max.	at $V_R$ Volts	Min.	Typ.	Max.	
BBY31	28	1.8	-	2.8	25	-	5.0	-	-
BBY40	28	26	-	32	3	5	-	6.5	-
		4.3	-	6.0	25				
FMMV105G	30	1.8	-	2.8	25	4.0	-	6.0	350
FMMV109	30	26	-	32	3	5.0	-	6.5	250
FMMV3102	30	26	-	25	3	4.5	-	-	300